

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): YAMAGATA et al.

Filed: Herewith

Title: SUBSTRATE MATERIAL FOR MOUNTING A SEMICONDUCTOR DEVICE, SUBSTRATE FOR MOUNTING A SEMICONDUCTOR DEVICE, SEMICONDUCTOR DEVICE, AND METHOD OF PRODUCING THE SAME

August 10, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend this application as follows:

IN THE SPECIFICATION:

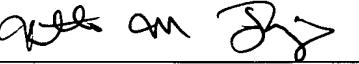
At the top of the first page, just under the title, insert:

1. --This is a Continuation-In-Part Divisional
 Continuation Substitute Application (MPEP 201.09) of
1(a) National Application No. 09/692,162 filed October 20, 2000, which is a Divisional of
Appln. No. 08/874,543, filed June 13, 1997
- 1(b) International Application No. PCT/___/
filed ___ which designated the U.S.--

2. --This application claims the benefit of U.S. Provisional Application No.
60/___, filed ___--

Respectfully submitted,

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Intellectual Property Group

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In re PATENT APPLICATION OF

Confirmation No.:

YAMAGATA et al.

Group Art Unit: (Unknown)

Divisional of: 09/692,162

Examiner: (Unknown)

Parent Filed: October 20, 2000

#5/B
J. F. G.
9/3/02

Divisional Filed: August 10, 2001

Title: SUBSTRATE MATERIAL FOR MOUNTING
A SEMICONDUCTOR DEVICE, SUBSTRATE
FOR MOUNTING A SEMICONDUCTOR DEVICE,
SEMICONDUCTOR DEVICE, AND METHOD
OF PRODUCING THE SAME

August 10, 2001

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PRELIMINARY AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified Application as follows.

IN THE SPECIFICATION:

Page 1, line 13, change the paragraph to read:

B1
2. Description of the Prior Art

B2
Page 1, lines 14-21, change the paragraph to read:

With the recent remarkable increases of the processing rate of semiconductor devices and the degree of integration in semiconductor devices, the heat generated by semiconductor elements has come to produce influences that are not negligible. As a result, substrate materials for mounting semiconductor devices have come to be required to have a high thermal conductivity for efficiently removing the heat generated by semiconductor elements.

B3
Page 9, lines 21-26, change the paragraph to read:

Aluminum/silicon carbide composite alloys have a high degree of hardness.

Therefore it is very difficult to form a shape, especially a complex shape such as heatsink by